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SPECIFICATION

TO ALL WHOM IT MAY CONCERN:

BE IT KNOWN THAT I, Nobutaka Taniguchi, a citizen of Japan residing at Kawasaki, Japan have invented certain new and useful improvements in

DELAY TIME ADJUSTING METHOD OF DELAYING A PHASE OF AN  
OUTPUT SIGNAL UNTIL A PHASE DIFFERENCE BETWEEN AN INPUT  
SIGNAL AND THE OUTPUT SIGNAL BECOMES AN INTEGRAL NUMBER  
OF PERIODS OTHER THAN ZERO

of which the following is a specification : -

TITLE OF THE INVENTION

DELAY TIME ADJUSTING METHOD OF DELAYING A  
PHASE OF AN OUTPUT SIGNAL UNTIL A PHASE DIFFERENCE  
BETWEEN AN INPUT SIGNAL AND THE OUTPUT SIGNAL  
5 BECOMES AN INTEGRAL NUMBER OF PERIODS OTHER THAN  
ZERO

BACKGROUND OF THE INVENTION

1. Field of the Invention

10 The present invention generally relates to  
a delay time adjusting circuit and, more  
particularly, to a delay time adjusting circuit and  
a delay time adjusting method which circuit and  
method adjust a delay time of a signal transmitted  
15 in a semiconductor integrated circuit.

2. Description of the Related Art

Conventionally, a semiconductor integrated  
circuit, such as a DDR(Double Data Rate)-SDRAM,  
which is required to operate at high speed and has a  
20 DLL (Delay Locked Loop) circuit mounted thereon,  
comprises a delay time adjusting circuit to adjust a  
phase of a clock signal.

FIG.1 is a circuit diagram of a  
conventional delay time adjusting circuit. As shown  
25 in FIG.1, the conventional delay time adjusting  
circuit comprises an input buffer 1, an output  
buffer 5, frequency dividers 2 and 4, a DLL array 3,  
a dummy circuit 6, a phase comparator 8 and a delay  
adjuster 10.

30 In this conventional delay time adjusting  
circuit, a clock signal is input into the input  
buffer 1, which outputs a signal Cin. The frequency  
divider 2 and the DLL array 3 are connected to the  
input buffer 1. The frequency divider 4 and the  
35 output buffer 5 are connected to an output terminal  
of the DLL array 3. The frequency divider 2 outputs  
a target clock signal tclk. The DLL array 3 outputs

a signal Cout. The output buffer 5 outputs a clock signal delayed by the DLL array 3. The frequency division rates of the frequency dividers 2 and 4 are equal.

5           The dummy circuit 6 is connected to the frequency divider 4 and outputs a delay clock signal dclk. The phase comparator 8 is connected to the frequency divider 2 and an output terminal of the dummy circuit 6, and feeds back a result signal  
10 'out' to the delay adjuster 10, according to the supplied target clock signal tclk and the fed-back delay clock signal dclk. An output terminal of the delay adjuster 10 is connected to the DLL array 3. The delay adjuster 10 supplies a control signal CS  
15 to the DLL array 3.

FIG.2 is a circuit diagram of the DLL array 3 shown in FIG.1. As shown in FIG.2, the DLL array 3 comprises a switching unit 31 including a plurality of parallel-connected switches SW1 to SWn,  
20 and inverters INV1 to INVn respectively arranged to correspond to the switches SW1 to SWn. Switching of the switches SW1 to SWn included in the switching unit 31 is controlled by the controlling signal CS supplied by the delay adjuster 10. The signal Cin  
25 is delayed by a time  $t_d$  in each of the inverters INV1 to INVn.

In the above-mentioned delay time adjusting circuit, supposing that a delay time at the input buffer 1 is  $d_1$  and a delay time at the  
30 output buffer 5 is  $d_2$ , a delay time at the dummy circuit 6 is  $(d_1 + d_2)$ . Also, supposing that a delay time of the DLL array 3 is  $d_3$ , the clock signal input into the input buffer 1 and consequently output from the output buffer 5 is  
35 delayed by a time  $(d_1 + d_2 + d_3)$ .

Also, supposing that delay times at the frequency dividers 2 and 4 are  $d_4$ , the clock signal

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input into the input buffer 1 and then input into the phase comparator 8 as the target clock signal tclk is delayed by a time  $(d1 + d4)$ . On the other hand, the clock signal input into the input buffer 1 and consequently input into the phase comparator 8 as the delay clock signal dclk is delayed by a time  $(d1 + d3 + d4 + (d1 + d2))$ .

Accordingly, a difference in the delay times between the target clock signal tclk and the delay clock signal dclk is  $(d1 + d2 + d3)$ . This difference equals the delay time  $(d1 + d2 + d3)$  of the clock signal input into the input buffer 1 and consequently output from the output buffer 5. Thereby, in order to match phases of the clock signal input into the input buffer 1 and the clock signal output from the output buffer 5, the delay adjuster 10 adjusts the delay time  $d3$  of the DLL array 3 so that the difference  $(d1 + d2 + d3)$  in the delay times between the target clock signal tclk and the delay clock signal dclk equals a time corresponding to a number  $n$  (1, 2 or other natural numbers) of clocks of the clock signal.

Next, a description will be given, with reference to FIG.3, of an operation of the above-mentioned conventional delay time adjusting circuit shown in FIG.1. FIG.3 is a waveform diagram indicating the operation of the conventional delay time adjusting circuit shown in FIG.1. First, a signal  $C_{in}$  indicated by FIG.3-(a) is divided by four by the frequency divider 2, as indicated by FIG.3-(b), and then is supplied to the phase comparator 8 as the target clock signal tclk. On the other hand, in the DLL array 3, the signal  $C_{in}$  is delayed by a predetermined time, generating a signal  $C_{out}$  indicated by FIG.3-(c). Then, the signal  $C_{out}$  is divided by four by the frequency divider 4, generating a monitor clock signal mclk indicated by

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FIG.3-(d).

Since the frequency dividers 2 and 4 are supposed to have the same structure, a delay time VD of the monitor clock signal mclk with respect to the target clock signal tclk means a delay time in the DLL array 3. It is noted that variable delay stages of the DLL array 3 are assumed to be minimum stages that provide a minimum delay time.

The monitor clock signal mclk is delayed by a fixed time FD regardless of a frequency thereof in the dummy circuit 6, generating a delay clock signal dclk indicated by FIG.3-(e). Then, phases of the delay clock signal dclk and the target clock signal tclk are compared in the phase comparator 8, which judges that the phase of the delay clock signal dclk is a time TD ahead of the phase of the target clock signal tclk. The phase comparator 8 supplies the delay adjuster 10 with a result signal 'out' indicating that the phase of the delay clock signal dclk is the time TD ahead of the phase of the target clock signal tclk.

Then, the delay adjuster 10 supplies the DLL array 3 with a control signal CS according to the result signal 'out'. Then, the delay time in the DLL array 3 is lengthened by the time TD. The above-mentioned operation generates a signal Lon, indicated by FIG.3-(f), as a delay clock signal dclk so that the phase of the delay clock signal dclk is matched to the phase of the target clock signal tclk.

Next, a description will be given, with reference to FIG.4, of an operation of the above-mentioned conventional delay time adjusting circuit shown in FIG.1, in a case where a clock signal having a higher frequency is input into the input buffer 1, as a semiconductor integrated circuit is increasingly required to operate at high speed. FIG.4 is a waveform diagram indicating the operation

of the conventional delay time adjusting circuit shown in FIG.1. In this case, a signal Cin indicated by FIG.4-(a), which is supplied to the frequency divider 2 and the DLL array 3, has a higher frequency than the signal Cin indicated by FIG.3-(a). The signal Cin indicated by FIG.4-(a) is divided by four by the frequency divider 2, as in the case shown in FIG.3, and then is supplied to the phase comparator 8 as a target clock signal tclk indicated by FIG.4-(b). On the other hand, in the DLL array 3, the signal Cin is delayed by a predetermined time, generating a signal Cout indicated by FIG.4-(c). Then, the signal Cout is divided by four by the frequency divider 4, generating a monitor clock signal mclk indicated by FIG.4-(d).

Since the frequency dividers 2 and 4 are supposed to have the same structure, a delay time VD of the monitor clock signal mclk to the target clock signal tclk means a delay time in the DLL array 3. It is noted that the variable delay stages of the DLL array 3 are assumed to be minimum stages that provide a minimum delay time.

The monitor clock signal mclk is delayed by the fixed time FD regardless of a frequency thereof in the dummy circuit 6, generating a delay clock signal dclk indicated by FIG.4-(e). Then, phases of the delay clock signal dclk and the target clock signal tclk are compared in the phase comparator 8.

However, as indicated by FIG.4-(b) and FIG.4-(e), when the frequency of the signal Cin is high, the sum of the delay time VD of the minimum stages in the DLL array 3 and the fixed time FD, which is fixed regardless of a frequency, delayed in the dummy circuit 6 may cause the phase of the delay clock signal dclk to be behind the phase of the

target clock signal tclk.

There is a problem in this case that since the phase of the delay clock signal dclk is already behind the phase of the target clock signal tclk, the delay time in the DLL array 3 cannot be adjusted so that the phase of the delay clock signal dclk is matched to the phase of the target clock signal tclk by using a first clock of the target clock signal tclk as a target. A case like this is referred to as a so-called underflow state.

#### SUMMARY OF THE INVENTION

It is a general object of the present invention to provide an improved and useful delay time adjusting circuit and a delay time adjusting method in which circuit and method the above-mentioned problems are eliminated.

A more specific object of the present invention is to provide a delay time adjusting circuit and a delay time adjusting method which circuit and method can easily adjust a delay time of a signal even when the signal has a high frequency.

In order to achieve the above-mentioned objects, there is provided according to one aspect of the present invention a delay time adjusting method of adjusting a delay time of an input signal so that a phase of the input signal and a phase of an output signal match each other, the method comprising the step of:

delaying the phase of the output signal until a phase difference between the phase of the input signal and the phase of the output signal becomes N periods, where N is an integer other than zero.

According to the present invention, a degree of freedom can be enhanced when delaying the phase of the output signal so as to match the phases

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of the input signal and the output signal. Thus, the phases of the input signal and the output signal can be easily matched regardless of a frequency of the input signal.

5           Additionally, in the present invention, the delay time adjusting method may further comprise a step of producing the output signal by delaying the input signal by a DLL circuit. In this case, by  
10 circuit, the delay time of the input signal can be easily adjusted.

          In order to achieve the above-mentioned objects, there is also provided according to another aspect of the present invention a delay time  
15 adjusting method of adjusting a delay time of an input first periodic signal so that a phase of the input first periodic signal and a phase of an output second periodic signal match each other, the method comprising the step of:

20           adjusting the delay time so that, when a phase of a predetermined rising edge of the output second periodic signal is behind a phase of a predetermined rising edge of the input first  
25 the output second periodic signal matches a rising edge of the input first periodic signal, a phase of the rising edge being behind and nearest to the phase of the predetermined rising edge of the output second periodic signal.

30           According to the present invention, when the phase of the predetermined rising edge of the output second periodic signal is, at an initial state, behind the phase of the predetermined rising  
35 of the input first periodic signal and the output second periodic signal can be easily matched. Therefore, even when the input first periodic signal

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In order to achieve the above-mentioned objects, there is also provided according to still another aspect of the present invention a delay time adjusting circuit for adjusting a delay time of an input first periodic signal so that a phase of the input first periodic signal and a phase of an output second periodic signal match each other, the circuit comprising:

delaying means for delaying the input first periodic signal so as to generate the output second periodic signal;

phase-detecting means for detecting whether a phase of a predetermined rising edge of the output second periodic signal is behind a phase of a first rising edge of the input first periodic signal; and

adjusting means for controlling the delaying means so that, when the phase of the predetermined rising edge is judged to be behind the phase of the first rising edge by the phase-detecting means, the delaying means delays the phase of the output second periodic signal until the phase of the predetermined rising edge and a phase of a second rising edge of the input first periodic signal match each other, the second rising edge being one period behind the first rising edge.

Additionally, in the present invention, the adjusting means may control the delaying means so that, after the phase of the predetermined rising edge and the phase of the second rising edge match each other, the phase of the predetermined rising edge and the phase of the second rising edge match each other all the time within a tolerable range.

According to the present invention, the output second periodic signal having a phase matching a phase of the input first periodic signal

can be steadily output. Therefore, the delay time adjusting method and circuit according to the present invention can be more reliable in operation.

Other objects, features and advantages of the present invention will become more apparent from the following detailed description when read in conjunction with the accompanying drawings.

#### BRIEF DESCRIPTION OF THE DRAWINGS

10 FIG.1 is a circuit diagram of a conventional delay time adjusting circuit;

FIG.2 is a circuit diagram of a DLL (Delay Locked Loop) array shown in FIG.1;

15 FIG.3 is a first waveform diagram indicating an operation of the conventional delay time adjusting circuit shown in FIG.1;

FIG.4 is a second waveform diagram indicating an operation of the conventional delay time adjusting circuit shown in FIG.1;

20 FIG.5 is a circuit diagram of a delay time adjusting circuit according to an embodiment of the present invention;

FIG.6 is a first waveform diagram indicating an operation of the delay time adjusting circuit shown in FIG.5;

FIG.7 is a second waveform diagram indicating an operation of the delay time adjusting circuit shown in FIG.5;

30 FIG.8 is a circuit diagram of a phase comparator shown in FIG.5;

FIG.9 is a waveform diagram indicating an operation of the phase comparator shown in FIG.8 in a case where a first clock of a delay clock signal is behind a first clock of a target clock signal;

35 FIG.10 is a waveform diagram indicating an operation of the phase comparator shown in FIG.8 in a case where a first clock of a delay clock signal

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is ahead of a first clock of a target clock signal;

FIG.11 is a circuit diagram of a state detection circuit shown in FIG.5; and

FIG.12 is a circuit diagram of a state judgment circuit shown in FIG.5.

#### DETAILED DESCRIPTION OF THE PREFERRED EMBODIMENTS

A description will now be given, with reference to the drawings, of embodiments according to the present invention. Elements in the drawings that are identical or equivalent are referenced by the same characters.

FIG.5 is a circuit diagram of a delay time adjusting circuit according to an embodiment of the present invention. As shown in FIG.5, the delay time adjusting circuit according to the present embodiment comprises the input buffer 1, the output buffer 5, the frequency dividers 2 and 4, a DLL array 7, the dummy circuit 6, the phase comparator 8, a delay adjuster 24, a state judgment circuit 20 and a state detection circuit 22.

It should be noted that the frequency divider 2 may be considered to be an element that determines a target used in adjusting a phase of a signal. The second frequency divider 12 may be considered to be an element that determines how frequently the phase of a signal has a chance to be adjusted.

In the above-mentioned delay time adjusting circuit, a clock signal is input into the input buffer 1. The frequency divider 2 and the DLL array 7 are connected to the input buffer 1. The frequency divider 4 and the output buffer 5 are connected to an output terminal of the DLL array 7. The frequency divider 2 outputs the target clock signal tclk. The dummy circuit 6 is connected to the frequency divider 4 and outputs the delay clock

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signal dclk. The phase comparator 8 is connected to the frequency divider 2 and the output terminal of the dummy circuit 6, and supplies the result signal 'out' indicating a result of a phase comparison to the state judgment circuit 20 and the state detection circuit 22.

The state detection circuit 22 receives a power-on reset signal resz activated to a high level when the DLL array 7 starts a delay time adjustment, and supplies a state detection result signal fstz to the state judgment circuit 20. The state judgment circuit 20 supplies a comparison result signal upz to the delay adjuster 24. An output terminal of the delay adjuster 24 is connected to the DLL array 7, and the delay adjuster 24 supplies the control signal CS to the DLL array 7. Frequency division rates of the frequency dividers 2 and 4 are set to, for example, four. As mentioned hereinafter, the delay time adjusting circuit shown in FIG.5 requires a smaller number of delay stages (the inverters INV1 to INVn) to be included in the DLL array 7 than that of a conventional technology.

Next, a description will be given, with reference to FIG.6, of an operation of the above-mentioned delay time adjusting circuit shown in FIG.5. FIG.6 is a waveform diagram indicating the operation of the delay time adjusting circuit shown in FIG.5. First, a signal Cin indicated by FIG.6-(a) is divided by four by the frequency divider 2, as indicated by FIG.6-(b), and then is supplied to the phase comparator 8 as the target clock signal tclk. On the other hand, in the DLL array 7, the signal Cin is delayed by a predetermined time, generating a signal Cout indicated by FIG.6-(c). Then, the signal Cout is divided by four by the frequency divider 4, generating a monitor clock signal mclk indicated by FIG.6-(d).

Since the frequency dividers 2 and 4 are supposed to have the same structure, a delay time VD of the monitor clock signal mclk to the target clock signal tclk means a delay time in the DLL array 7.

- 5 It is noted that variable delay stages of the DLL array 7 are assumed to be minimum stages that provide a minimum delay time.

The monitor clock signal mclk is delayed by a fixed time FD regardless of a frequency thereof in the dummy circuit 6, generating a delay clock signal dclk indicated by FIG.6-(e). Then, phases of the delay clock signal dclk and the target clock signal tclk are compared in the phase comparator 8, which judges that the phase of the delay clock  
10 signal dclk is a time TD ahead of the phase of the target clock signal tclk. The phase comparator 8 supplies the state judgment circuit 20 and the state detection circuit 22 with a result signal 'out' indicating that the phase of the delay clock signal  
15 dclk is the time TD ahead of the phase of the target clock signal tclk.  
20

At this time, the state detection circuit 22, as described in detail later, receives the power-on reset signal resz activated to a high level  
25 when the DLL array 7 starts a delay time adjustment, and supplies the state detection result signal fstz at a high level to the state judgment circuit 20. Thereby, the state judgment circuit 20, as described in detail later, supplies the comparison result  
30 signal upz at a high level to the delay adjuster 24.

The delay adjuster 24 supplies the DLL array 7 with the control signal CS according to the supplied comparison result signal upz at a high level. Then, the delay time in the DLL array 7 is  
35 lengthened by the time TD. The above-mentioned operation generates a signal Lon, indicated by FIG.6-(f), as a delay clock signal dclk so that the

FIG. 6-13

phase of the delay clock signal dclk is matched to and locked on the phase of the target clock signal tclk. It is noted that "locking-on" means matching the phases of the delay clock signal dclk and the target clock signal tclk all the time within a tolerable range. It is also noted that the tolerable range here means, for example, a margin of an operating frequency that guarantees a normal operation in a specification of a semiconductor integrated circuit on which the delay time adjusting circuit is mounted.

Next, a description will be given, with reference to FIG.7, of an operation of the above-mentioned delay time adjusting circuit shown in FIG.5, in a case where a clock signal having a higher frequency is input into the input buffer 1, as a semiconductor integrated circuit is increasingly required to operate at high speed. FIG.7 is a waveform diagram indicating the operation of the delay time adjusting circuit shown in FIG.5. In this case, a signal Cin indicated by FIG.7-(a), which is supplied to the frequency divider 2 and the DLL array 7, has a higher frequency than the signal Cin indicated by FIG.6-(a). The signal Cin indicated by FIG.7-(a) is divided by four by the frequency divider 2, as in the case shown in FIG.6, and then is supplied to the phase comparator 8 as a target clock signal tclk indicated by FIG.7-(b).

On the other hand, in the DLL array 7, the signal Cin is delayed by a predetermined time, generating a signal Cout indicated by FIG.7-(c). Then, the signal Cout is divided by four by the frequency divider 4, generating a monitor clock signal mclk indicated by FIG.7-(d).

Since the frequency dividers 2 and 4 are supposed to have the same structure, a delay time VD of the monitor clock signal mclk with respect to the

target clock signal tclk means a delay time in the DLL array 7. It is noted that the variable delay stages of the DLL array 7 are assumed to be minimum stages that provide a minimum delay time.

5           The monitor clock signal mclk is delayed by the fixed time FD regardless of a frequency thereof in the dummy circuit 6, generating a delay clock signal dclk indicated by FIG.7-(e). Then, phases of the delay clock signal dclk and the target  
10 clock signal tclk are compared in the phase comparator 8.

          However, as indicated by FIG.7-(b) and FIG.7-(e), when the frequency of the signal Cin is high, the sum of the delay time VD of the minimum  
15 stages in the DLL array 7 and the fixed time FD, which is fixed regardless of a frequency, delayed in the dummy circuit 6 may cause the phase of the delay clock signal dclk to be behind the phase of the target clock signal tclk.

20           In this case, since the phase of the delay clock signal dclk is already behind the phase of the target clock signal tclk, the delay time in the DLL array 7 cannot be adjusted so that the phase of the delay clock signal dclk is matched to the phase of  
25 the target clock signal tclk by using a first rise (a transition from a low level to a high level, also referred to as "rising edge") of the target clock signal tclk as a target.

          At this time, the state detection circuit  
30 22 shown in FIG.5, regardless of a comparison result in the phase comparator 8, supplies the state detection result signal fstz at a high level to the state judgment circuit 20 according to the power-on reset signal resz supplied to the state detection  
35 circuit 22, as in the case shown in FIG.6. Therefore, the state judgment circuit 20 supplies the comparison result signal upz at a high level to



the delay adjuster 24. It is noted that the state detection circuit 22 and the state judgment circuit 20 are described in detail later.

Therefore, the delay adjuster 24 supplies  
5 the DLL array 7 with the control signal CS according to the supplied comparison result signal upz at a high level so as to lengthen the delay time in the DLL array 7.

By repeating the above-mentioned phase  
10 comparison and the lengthening of the delay time, the delay time in the DLL array 7 is further lengthened by a time AD so that a first clock (rise) of the delay clock signal dclk goes behind a second clock (rise) of the target clock signal tclk. At  
15 this point, the phase comparator 8 supplies a result signal 'out' at a low level to the state detection circuit 22. Subsequently, the state detection circuit 22 supplies a state detection result signal fstz at a low level to the state judgment circuit 20.  
20 Thereby, the state judgment circuit 20 is activated and supplies the delay adjuster 24 with the comparison result in the phase comparator 8 as a comparison result signal upz at a low level.

Then, the delay adjuster 24 supplies the  
25 DLL array 7 with a control signal CS according to the supplied comparison result signal upz at a low level so as to shorten the delay time in the DLL array 7. As a result of this, a signal Lon is generated as a delay clock signal dclk and locked on  
30 so that a first clock (rise) of the signal Lon is matched to the second clock (rise) of the target clock signal tclk, as indicated by FIG.7-(f).

Hereinafter, a description will be given,  
with reference to FIG.8 to FIG.10, of the phase  
35 comparator 8 shown in FIG.5. FIG.8 is a circuit diagram of the phase comparator 8 shown in FIG.5. As shown in FIG.8, the phase comparator 8 comprises

NAND circuits 80 to 85. The target clock signal tclk is supplied to the NAND circuits 81 and 82. The delay clock signal dclk is supplied to the NAND circuit 83. The result signal 'out' is output from an output terminal of the NAND circuit 84.

FIG.9 is a waveform diagram indicating an operation of the above-mentioned phase comparator 8 in a case where a first clock of a delay clock signal dclk is behind a first clock of a target clock signal tclk. FIG.9-(a) indicates the target clock signal tclk. FIG.9-(b) indicates the delay clock signal dclk. FIG.9-(c) indicates fluctuations of electric potential at an output node NA of the NAND circuit 81. FIG.9-(d) indicates fluctuations of electric potential at an output node NB of the NAND circuit 82. FIG.9-(e) indicates fluctuations of electric potential at an output node NC of the NAND circuit 80. FIG.9-(f) indicates fluctuations of electric potential at an output node ND of the NAND circuit 83. FIG.9-(g) indicates the result signal 'out'.

In the case shown in FIG.9, where the first clock of the delay clock signal dclk is behind the first clock of the target clock signal tclk, before a so-called rise time TA of the target clock signal tclk, the NAND circuits 84 and 85 latch the result signal 'out' at a high level or a low level. Then, at the rise time TA when the target clock signal tclk rises to a high level, the electric potential at the output node NB falls to a low level, and consequently, the result signal 'out' is fixed at the low level. Thereby, the phase comparator 8 supplies the state detection circuit 22 and the state judgment circuit 20 with the result signal 'out' at the low level. That is, the phase comparator 8 supplies the state detection circuit 22 and the state judgment circuit 20 with the result

signal 'out' indicating a judgment (decrease) that the first clock of the delay clock signal dclk is behind the first clock of the target clock signal tclk.

5                   FIG.10 is a waveform diagram indicating an operation of the above-mentioned phase comparator 8 in a case where a first clock of a delay clock signal dclk is ahead of a first clock of a target clock signal tclk. FIG.10-(a) indicates the target clock signal tclk. FIG.10-(b) indicates the delay clock signal dclk. FIG.10-(c) indicates fluctuations of electric potential at the output node NA of the NAND circuit 81. FIG.10-(d) indicates fluctuations of electric potential at the output node NB of the NAND circuit 82. FIG.10-(e) indicates fluctuations of electric potential at the output node NC of the NAND circuit 80. FIG.10-(f) indicates fluctuations of electric potential at the output node ND of the NAND circuit 83. FIG.10-(g) indicates the result signal 'out'.

10                   In the case shown in FIG.10, where the first clock of the delay clock signal dclk is ahead of the first clock of the target clock signal tclk, before the rise time TA of the target clock signal tclk, the NAND circuits 84 and 85 latch the result signal 'out' at a high level or a low level. Then, at the rise time TA when the target clock signal tclk rises to a high level, the electric potential at the output node NA falls to a low level, and consequently, the result signal 'out' is fixed at the high level. Thereby, the phase comparator 8 supplies the state detection circuit 22 and the state judgment circuit 20 with the result signal 'out' at the high level. That is, the phase comparator 8 supplies the state detection circuit 22 and the state judgment circuit 20 with the result signal 'out' indicating a judgment (increase) that

the first clock of the delay clock signal dclk is ahead of the first clock of the target clock signal tclk.

Next, a description will be given, with reference to FIG.11, of the state detection circuit 22 shown in FIG.5. FIG.11 is a circuit diagram of the state detection circuit 22 shown in FIG.5. As shown in FIG.11, the state detection circuit 22 comprises a delay circuit 40, inverters 41 to 45, a NOR circuit NOR1, gates GT1 and GT2, N-channel MOS transistors NT1 to NT7, and P-channel MOS transistors PT1 to PT8. The delay circuit 40 includes serially connected inverters 46 to 48 and MOS capacitors MC1 and MC2.

As shown in FIG.11, a result signal 'out' is supplied (from the phase comparator 8) to the NOR circuit NOR1 and the delay circuit 40. Therefore, the result signal 'out' and a signal which the delay circuit 40 produces by delaying the result signal 'out' by a predetermined time are input into the NOR circuit NOR1. A power-on reset signal resz, which transits from a low level to a high level when the delay time adjusting circuit according to the present embodiment gets energized, is supplied to an input terminal of the inverter 42 and a gate of the N-channel MOS transistor NT1. A source of the N-channel MOS transistor NT1 is connected to a grounding node Ng. A drain of the N-channel MOS transistor NT1 is connected via the inverter 45 to an output node Nout of the state detection circuit 22.

The gate GT1 connected between the inverter 43 and 44 and the gate GT2 connected between the inverter 44 and 45 are opened or closed depending on an output signal of the NOR circuit NOR1.

Next, a description will be given of an

operation of the state detection circuit 22. First, when a power supply is provided, the power-on reset signal *resz* at a high level is supplied to the gate of the N-channel MOS transistor NT1. Thereby, the  
5 N-channel MOS transistor NT1 is on, and a grounding voltage is supplied from the grounding node Ng to the inverter 45. Thereby, the inverter 45 inverts a signal at a low level so that a state detection result signal *fstz* at a high level is supplied to  
10 the output node Nout of the state detection circuit 22.

At this time, since a low-level signal is supplied from the inverter 42 to gates of the P-channel MOS transistors PT1 to PT2, the P-channel  
15 MOS transistors PT1 to PT2 become on. Thereby, power supply voltages *vcc* are supplied from power supply nodes Nv to the inverters 43 and 44 so that a low-level signal is supplied to gates of the N-channel MOS transistor NT3 and NT5. Thereby, the N-  
20 channel MOS transistor NT3 and NT5 become off.

As described above, at an initial state, the state detection circuit 22 is deactivated and outputs the state detection result signal *fstz* fixed at a high level. Then, when the result signal 'out' supplied from the phase comparator 8 changes from a  
25 high level to a low level, a low-level signal is input into one input terminal of the NOR circuit NOR1. However, while the result signal 'out' at a low level is transmitted through the delay circuit 40, a low-level signal is still supplied to the  
30 other input terminal of the NOR circuit NOR1. Therefore, during this time, the NOR circuit NOR1 outputs a high-level signal.

Thereby, the gates GT1 and GT2 are opened  
35 so that an output signal of the inverter 43 at a low level is transmitted through the gate GT1 to the inverter 44. Subsequently, the inverter 44

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transmits an output signal at a high level through the gate GT2 to the inverter 45. Accordingly, in this case, a signal at a low level is supplied from the inverter 45 to the output node Nout.

5           As described above, only when the result signal 'out' supplied from the phase comparator 8 transits from a high level to a low level, the state detection circuit 22 outputs a state detection result signal fstz at a low level.

10           Next, a description will be given, with reference to FIG.12, of the state judgment circuit 20 shown in FIG.5. FIG.12 is a circuit diagram of the state judgment circuit 20 shown in FIG.5. As shown in FIG.12, the state judgment circuit 20  
15           comprises a NOR circuit NOR2 and an inverter 49 connected thereto. A result signal 'out' supplied from the phase comparator 8 is input into one input terminal of the NOR circuit NOR2. A state detection result signal fstz supplied from the state detection  
20           circuit 22 is input into the other input terminal of the NOR circuit NOR2. A comparison result signal upz is supplied from an output terminal of the inverter 49 to the delay adjuster 24.

25           Next, a description will be given of an operation of the state judgment circuit 20. At an initial state, as described above, since a state detection result signal fstz at a high level is supplied to the NOR circuit NOR2, a low-level signal is continuously supplied to the inverter 49  
30           independent of a logical level of the result signal 'out'. Therefore, a comparison result signal upz at a high level is supplied from the inverter 49 to the delay adjuster 24. It is noted here that, as described above, the delay adjuster 24, when  
35           supplied with a comparison result signal upz at a high level, controls the switching unit 31 of the DLL array 7 so as to lengthen a delay time in the

5           The state judgment circuit 20 continues to  
output the comparison result signal upz at a high  
level to the delay adjuster 24 until a state  
detection result signal fstz at a low level is  
supplied from the state detection circuit 22 to the  
10 state judgment circuit 20. Then, when the state  
detection result signal fstz at a low level is  
supplied from the state detection circuit 22 to the  
state judgment circuit 20, since the NOR circuit  
NOR2 is activated, the state judgment circuit 20  
15 supplies the delay adjuster 24 with a signal at the  
same logical level as a result signal 'out' supplied  
from the phase comparator 8 as a comparison result  
signal upz.

As described above, according to the delay time adjusting circuit of the present embodiment, when a first clock of a delay clock signal dclk is ahead of a first clock of a target clock signal tclk at an initial state, the delay clock signal dclk is further delayed so that the first clock (rise) of the delay clock signal dclk is matched to the first clock (rise) of the target clock signal tclk.

Even in a case where a clock signal has a higher frequency and the DLL array 7 has minimum stages that provide a minimum delay time, when a first clock of a delay clock signal dclk is behind a first clock of a target clock signal tclk, the delay clock signal dclk is further delayed so that the first clock (rise) of the delay clock signal dclk is matched to a second clock (rise) of the target clock signal tclk.

Therefore, even when a clock signal has a higher frequency, a phase of a clock signal can be

adjusted easily, avoiding the underflow state which a conventional technology suffers. This allows for expanding an operating-frequency band of a semiconductor integrated circuit.

- 5           The present invention is not limited to the specifically disclosed embodiments, and variations and modifications may be made without departing from the scope of the present invention.

- 10           The present application is based on Japanese priority application No.2000-046225 filed on February 23, 2000, the entire contents of which are hereby incorporated by reference.

2000-046225